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PATENT ABSTRACTS OF JAPAN

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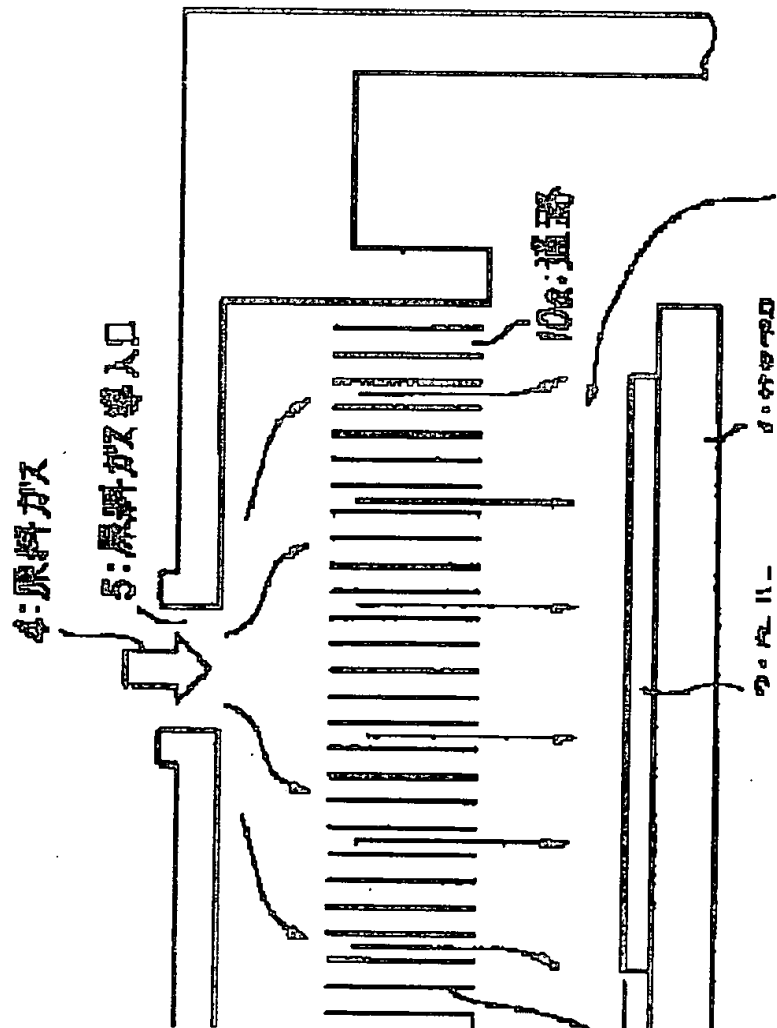
(74) Representative:

(54) VACUUM CVD
DEVICE

(57) Abstract:

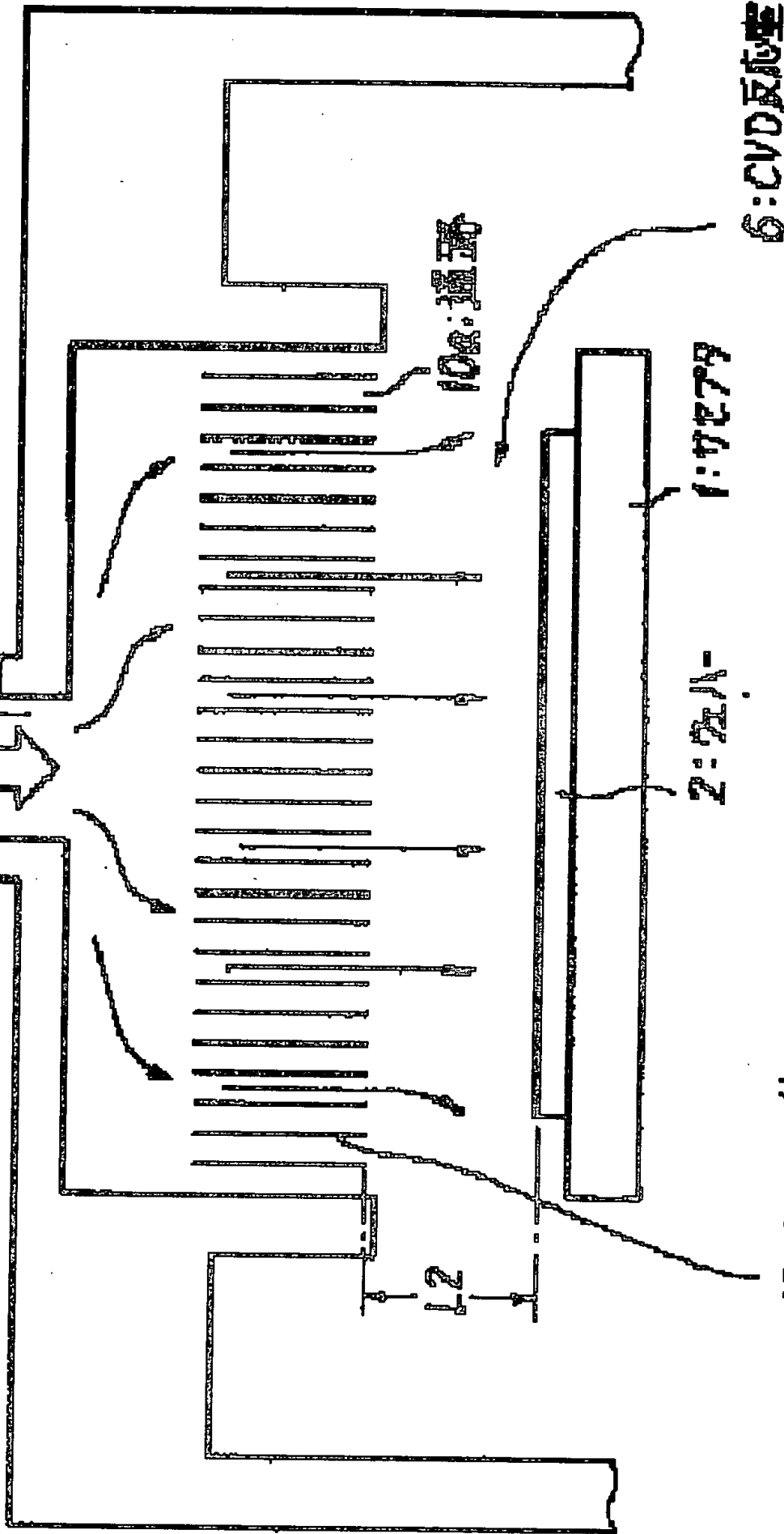
PURPOSE: To provide a vacuum CVD device which enables an improved step coverage and formation of buried layers contg. no seam part by filling contact holes, etc.

CONSTITUTION: This vacuum CVD device is provided with the CVD reaction chamber 6 having the CVD feed gas inlet 5, the supporting base 1, on which the substrate to be treated 2 is placed, and a gas distributing means that is disposed between the CVD feed gas inlet 5 and the substrate to be treated 2 to uniformly distribute the feed gas. The gas distributing means is provided with the plural passages 10a arranged in the approximately perpendicular direction to the surface of the substrate to be treated 2. Thus, any seam part in the contact holes is prevented from being generated.



4:原料ガス

5:原料ガス導入口



1:炉体

2:基板

6:CVD反応室

10:プロセス付シャフト

10a:通路

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